

# 74HC2G86; 74HCT2G86

Dual 2-input exclusive-OR gate

Rev. 03 — 7 May 2009

Product data sheet

## 1. General description

The 74HC2G86 and 74HCT2G86 are high-speed Si-gate CMOS devices. They provide two 2-input exclusive-OR gates.

The HC device has CMOS input switching levels and supply voltage range 2 V to 6 V.

The HCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

## 2. Features

- Wide supply voltage range from 2.0 V to 6.0 V
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
  - ◆ HBM JESD22-A114E exceeds 2000 V
  - ◆ MM JESD22-A115-A exceeds 200 V
- Specified from  $-40\text{ }^{\circ}\text{C}$  to  $+85\text{ }^{\circ}\text{C}$  and  $-40\text{ }^{\circ}\text{C}$  to  $+125\text{ }^{\circ}\text{C}$

## 3. Ordering information

Table 1. Ordering information

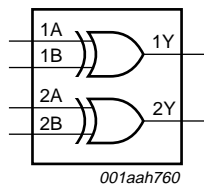
Type number	Package			
	Temperature range	Name	Description	Version
74HC2G86DP 74HCT2G86DP	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74HC2G86DC 74HCT2G86DC	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74HC2G86GD 74HCT2G86GD	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body $3 \times 2 \times 0.5$ mm	SOT996-2

## 4. Marking

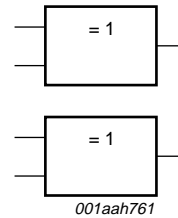
**Table 2. Marking code**

Type number	Marking code
74HC2G86DP	H86
74HCT2G86DP	T86
74HC2G86DC	H86
74HCT2G86DC	T86
74HC2G86GD	H86
74HCT2G86GD	T86

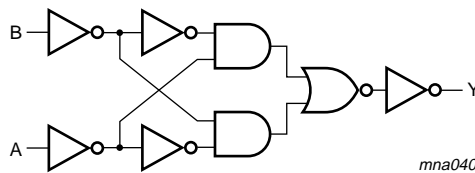
## 5. Functional diagram



**Fig 1. Logic symbol**



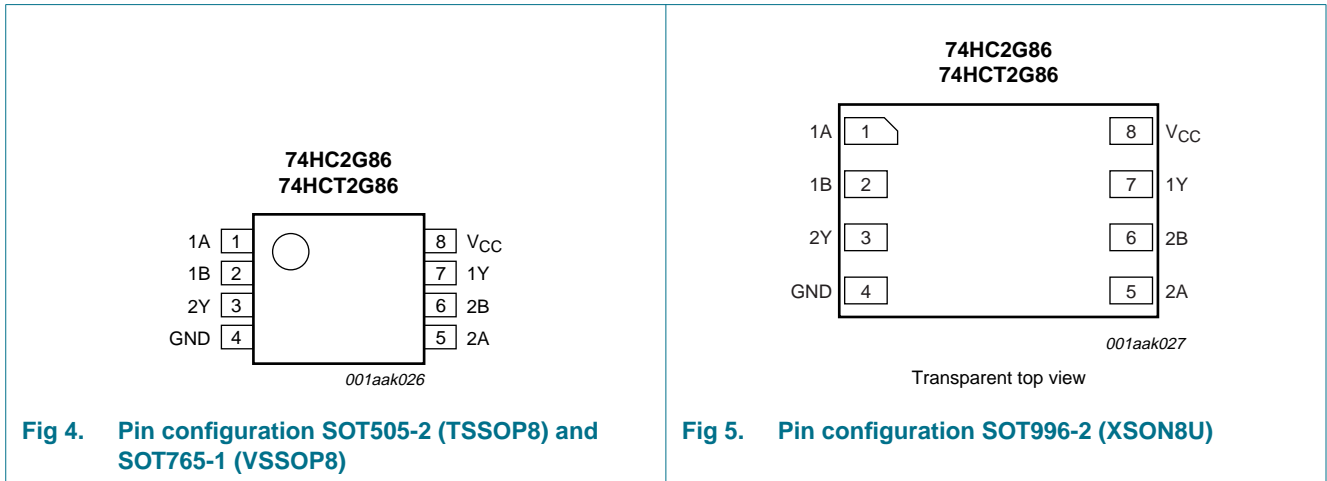
**Fig 2. IEC logic symbol**



**Fig 3. Logic diagram (one gate)**

## 6. Pinning information

### 6.1 Pinning



### 6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A, 2A	1, 5	data input
1B, 2B	2, 6	data input
GND	4	ground (0 V)
1Y, 2Y	7, 3	data output
V <sub>CC</sub>	8	supply voltage

## 7. Functional description

Table 4. Function table<sup>[1]</sup>

Input		Output
nA	nB	nY
L	L	L
L	H	H
H	L	H
H	H	L

[1] H = HIGH voltage level; L = LOW voltage level.

## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+7.0	V
$I_{IK}$	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	[1] -	±20	mA
$I_{OK}$	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$	[1] -	±20	mA
$I_O$	output current	$V_O = -0.5\text{ V}$ to $(V_{CC} + 0.5\text{ V})$	[1] -	25	mA
$I_{CC}$	supply current		[1] -	50	mA
$I_{GND}$	ground current		[1] -50	-	mA
$T_{stg}$	storage temperature		-65	+150	°C
$P_D$	dynamic power dissipation	$T_{amb} = -40\text{ °C}$ to $+125\text{ °C}$	[2] -	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of  $P_{tot}$  derates linearly with 2.5 mW/K.  
 For VSSOP8 package: above 110 °C the value of  $P_{tot}$  derates linearly with 8 mW/K.  
 For XSON8U package: above 118 °C the value of  $P_{tot}$  derates linearly with 7.8 mW/K.

## 9. Recommended operating conditions

**Table 6. Recommended operating conditions**

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC2G86			74HCT2G86			Unit
			Min	Typ	Max	Min	Typ	Max	
$V_{CC}$	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
$V_I$	input voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V
$V_O$	output voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V
$T_{amb}$	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.0\text{ V}$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5\text{ V}$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0\text{ V}$	-	-	83	-	-	-	ns/V

## 10. Static characteristics

**Table 7. Static characteristics**

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
<b>74HC2G86</b>										
$V_{IH}$	HIGH-level input voltage	$V_{CC} = 2.0\text{ V}$	1.5	1.2	-	1.5	-	1.5	-	V
		$V_{CC} = 4.5\text{ V}$	3.15	2.4	-	3.15	-	3.15	-	V
		$V_{CC} = 6.0\text{ V}$	4.2	3.2	-	4.2	-	4.2	-	V

**Table 7. Static characteristics ...continued**  
 Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V <sub>CC</sub> = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V <sub>CC</sub> = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>								
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 4.5 V	4.18	4.32	-	4.13	-	3.7	-	V
		I <sub>O</sub> = -5.2 mA; V <sub>CC</sub> = 6.0 V	5.68	5.81	-	5.63	-	5.2	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>								
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I <sub>O</sub> = 5.2 mA; V <sub>CC</sub> = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 6.0 V	-	-	1.0	-	10	-	20	μA
C <sub>I</sub>	input capacitance		-	1.5	-	-	-	-	-	pF
<b>74HCT2G86</b>										
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; V <sub>CC</sub> = 4.5 V								
		I <sub>O</sub> = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = -4.0 mA	4.18	4.32	-	4.13	-	3.7	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> ; V <sub>CC</sub> = 4.5 V								
		I <sub>O</sub> = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 4.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 5.5 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 5.5 V	-	-	1.0	-	10	-	20	μA
ΔI <sub>CC</sub>	additional supply current	per input; V <sub>CC</sub> = 4.5 V to 5.5 V; V <sub>I</sub> = V <sub>CC</sub> - 2.1 V; I <sub>O</sub> = 0 A	-	-	300	-	375	-	410	μA
C <sub>I</sub>	input capacitance		-	1.5	-	-	-	-	-	pF

## 11. Dynamic characteristics

**Table 8. Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
<b>74HC2G86</b>										
t <sub>pd</sub>	propagation delay	nA, nB to nY; see <a href="#">Figure 6</a> [1]								
		V <sub>CC</sub> = 2.0 V	-	34	120	-	150	-	180	ns
		V <sub>CC</sub> = 4.5 V	-	11	20	-	25	-	36	ns
		V <sub>CC</sub> = 6.0 V	-	9.0	17	-	21	-	30	ns
t <sub>t</sub>	transition time	nY; see <a href="#">Figure 6</a> [2]								
		V <sub>CC</sub> = 2.0 V	-	18	75	-	95	-	110	ns
		V <sub>CC</sub> = 4.5 V	-	6	15	-	19	-	22	ns
		V <sub>CC</sub> = 6.0 V		5	13	-	16	-	20	ns
C <sub>PD</sub>	power dissipation capacitance	per buffer; C <sub>L</sub> = 50 pF; f <sub>i</sub> = 1 MHz; V <sub>I</sub> = GND to V <sub>CC</sub>	[3]	-	10	-	-	-	-	pF
<b>74HCT2G86</b>										
t <sub>pd</sub>	propagation delay	nA, nB to nY; see <a href="#">Figure 6</a> [1]								
		V <sub>CC</sub> = 4.5 V	-	11	19	-	23	-	48	ns
t <sub>t</sub>	transition time	nY; see <a href="#">Figure 6</a> [2]								
		V <sub>CC</sub> = 4.5 V	-	6	15	-	19	-	22	ns
C <sub>PD</sub>	power dissipation capacitance	per buffer; C <sub>L</sub> = 50 pF; f <sub>i</sub> = 1 MHz; V <sub>I</sub> = GND to V <sub>CC</sub>	[3]	-	9	-	-	-	-	pF

[1] t<sub>pd</sub> is the same as t<sub>PLH</sub> and t<sub>PHL</sub>.

[2] t<sub>t</sub> is the same as t<sub>TLH</sub> and t<sub>THL</sub>.

[3] C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f<sub>i</sub> = input frequency in MHz;

f<sub>o</sub> = output frequency in MHz;

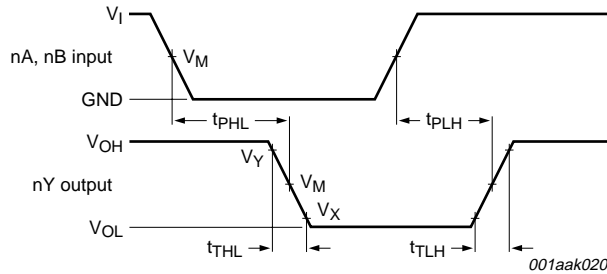
C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

Σ(C<sub>L</sub> × V<sub>CC</sub><sup>2</sup> × f<sub>o</sub>) = sum of the outputs.

12. Waveforms



Measurement points are given in [Table 9](#).  
 $V_{OL}$  and  $V_{OH}$  are typical output voltage levels that occur with the output load.

**Fig 6. Propagation delay data input (nA, nB) to data output (nY) and transition time output (nY)**

**Table 9. Measurement points**

Type	Input	Output		
	$V_M$	$V_M$	$V_X$	$V_Y$
74HC2G86	$0.5V_{CC}$	$0.5V_{CC}$	$0.1V_{CC}$	$0.9V_{CC}$
74HCT2G86	1.3 V	1.3 V	$0.1V_{CC}$	$0.9V_{CC}$

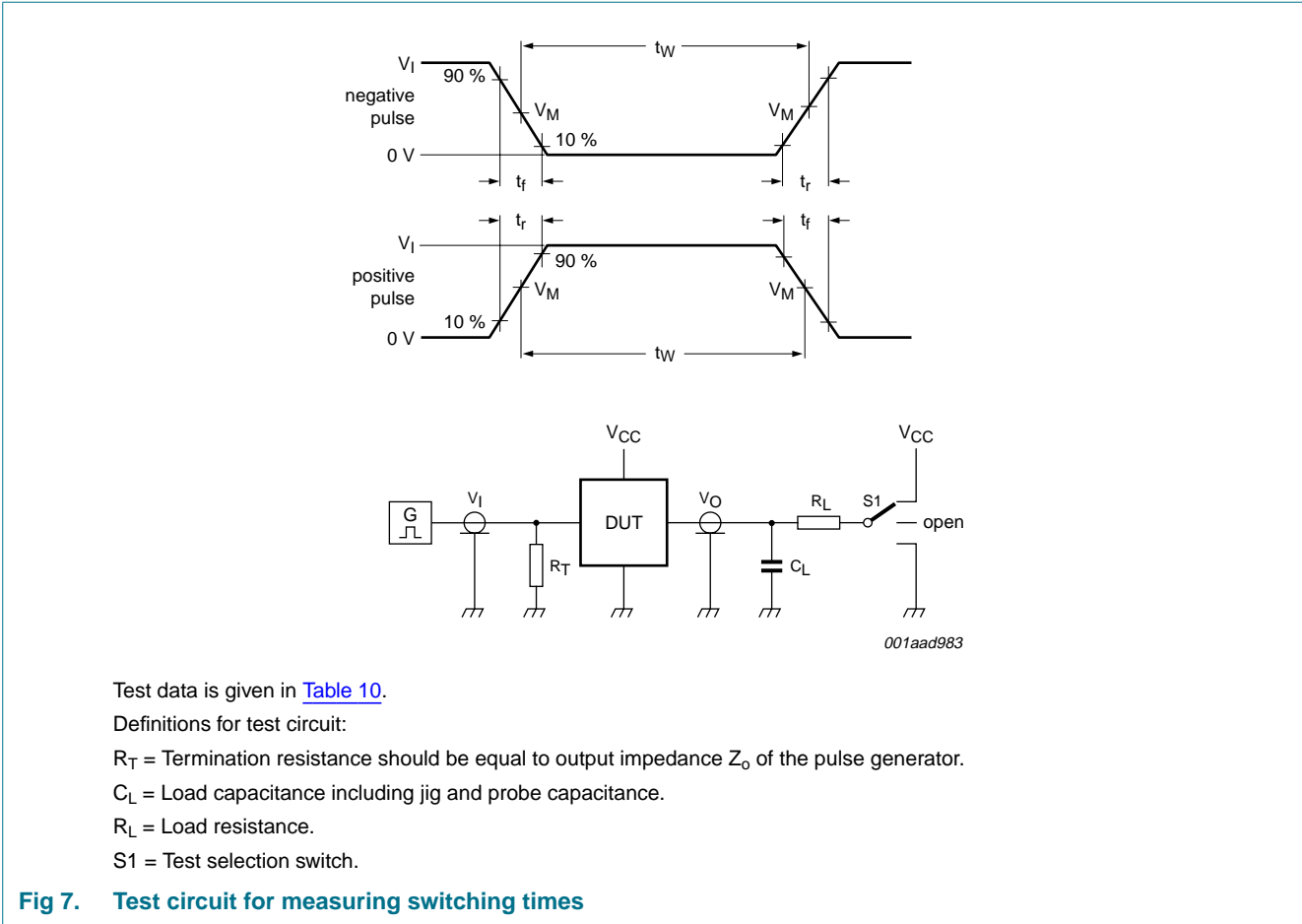


Table 10. Test data

Type	Input		Load			S1 position
	$V_I$	$t_r, t_f$	$C_L$	$R_L$	$t_{PHL}, t_{PLH}$	
74HC2G86	GND to $V_{CC}$	$\leq 6$ ns	50 pF	1 k $\Omega$	open	
74HCT2G86	GND to 3 V	$\leq 6$ ns	50 pF	1 k $\Omega$	open	



13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

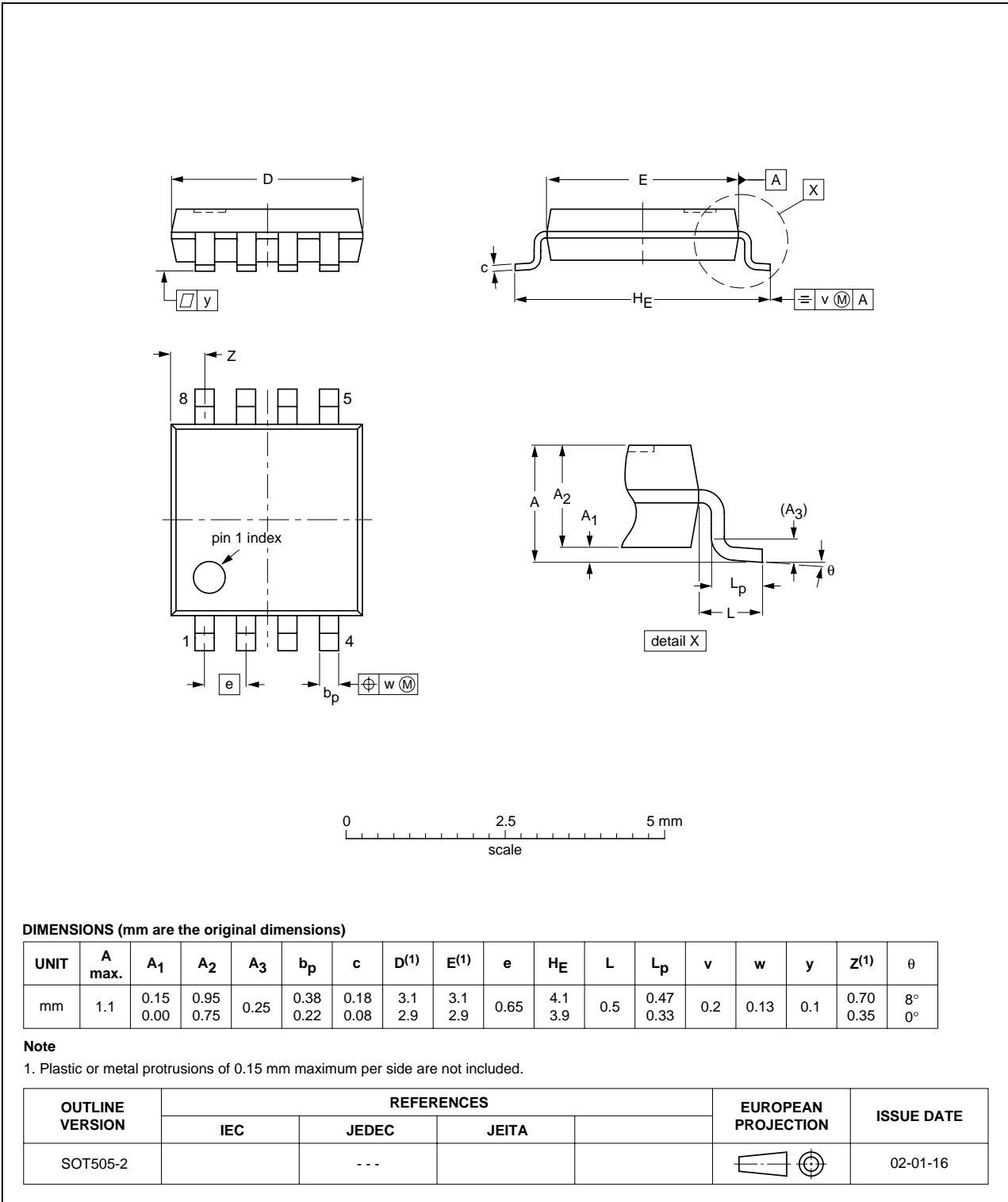


Fig 8. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

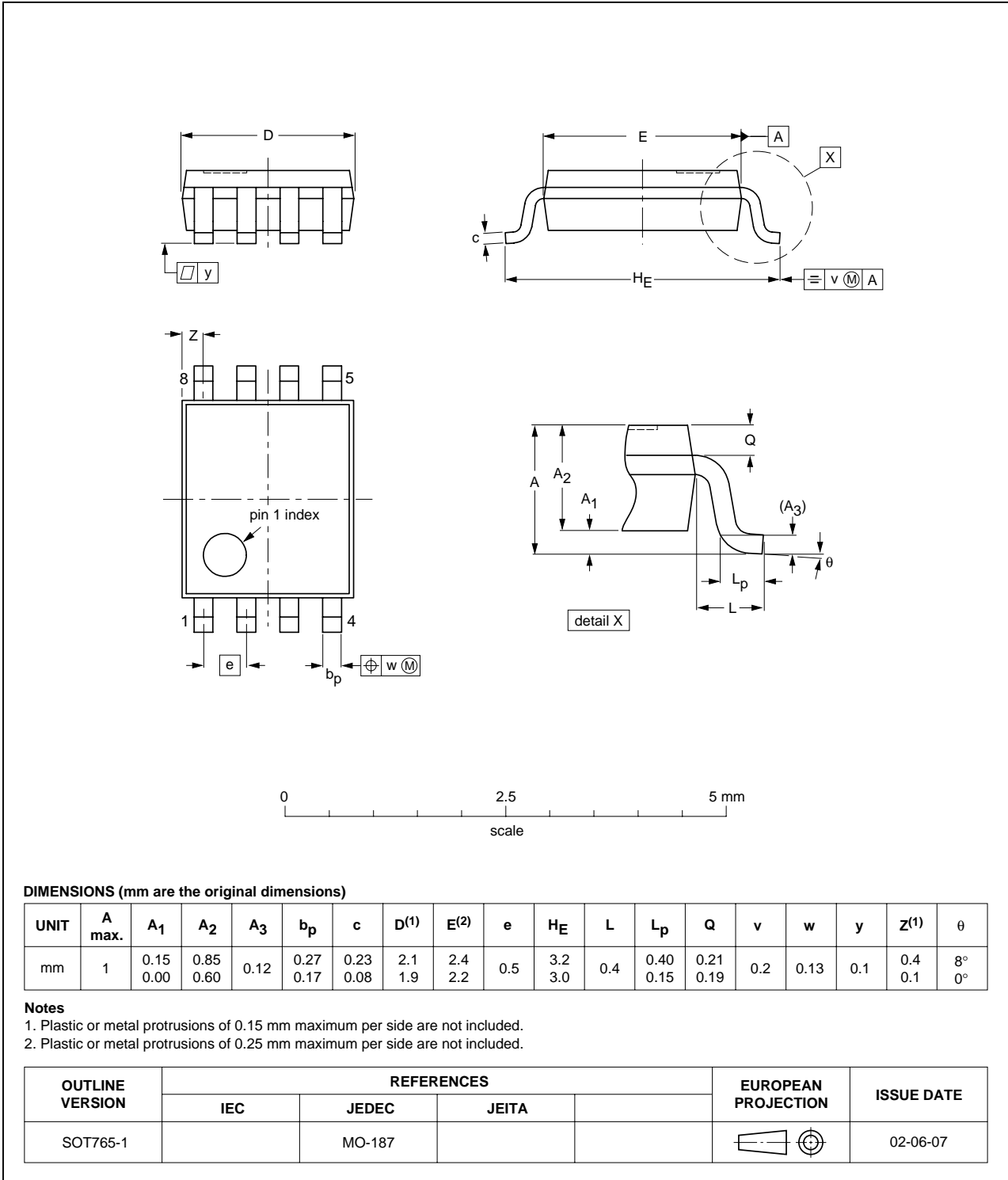


Fig 9. Package outline SOT765-1 (VSSOP8)

XSON8U: plastic extremely thin small outline package; no leads;  
8 terminals; UTLP based; body 3 x 2 x 0.5 mm

SOT996-2

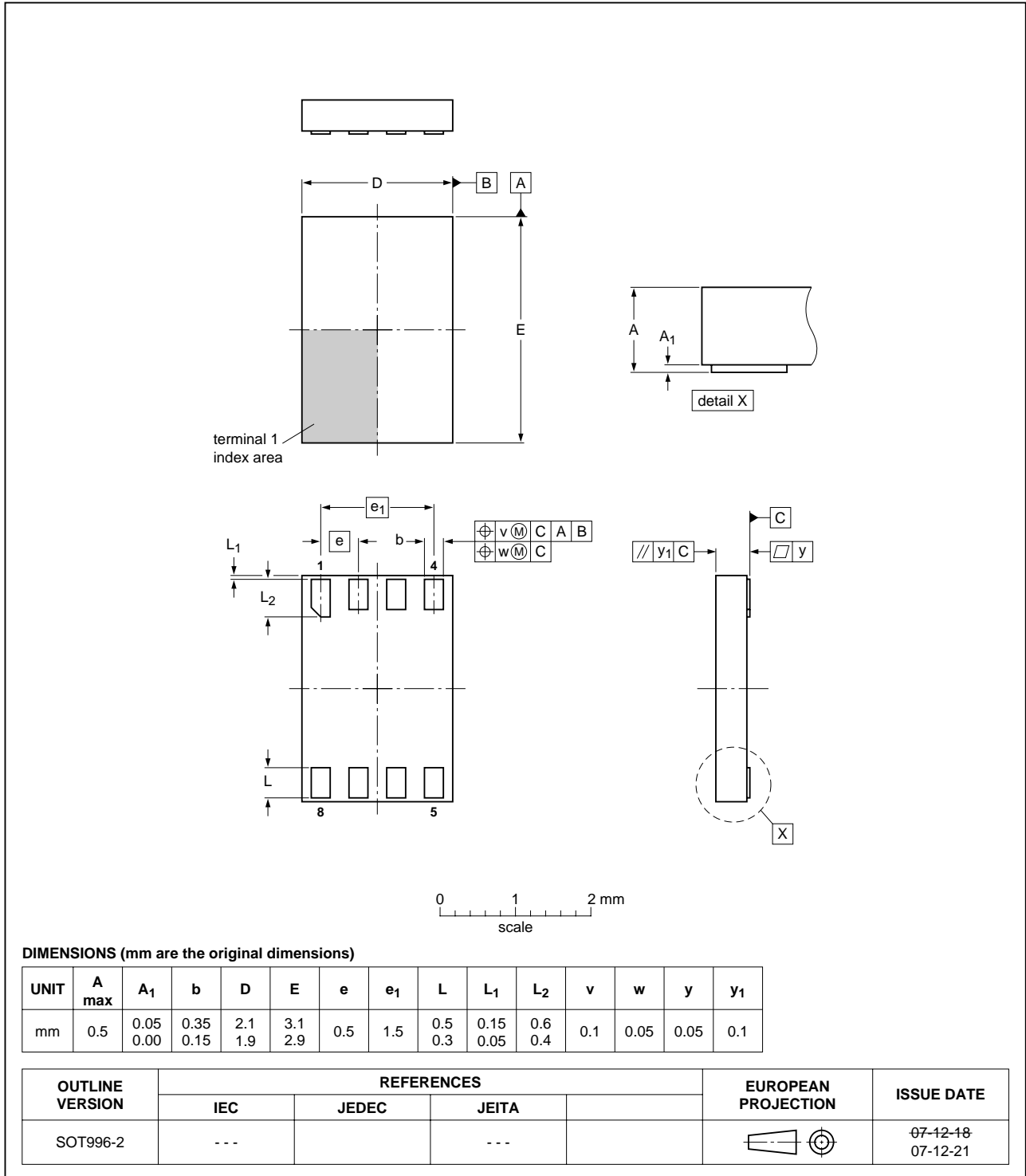


Fig 10. Package outline SOT996-2 (XSON8U)

## 14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

## 15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT2G86_3	20090507	Product data sheet	-	74HC_HCT2G86_2
Modifications:		<ul style="list-style-type: none"><li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li><li>Legal texts have been adapted to the new company name where appropriate.</li><li>Added type number 74HC2G86GD and 74HCT2G86GD (XSON8U package)</li></ul>		
74HC_HCT2G86_2	20030728	Product specification	-	74HC_HCT2G86_1
74HC_HCT2G86_1	20020717	Product specification	-	-

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### 16.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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